Amendments to the Claims

Applicants request amendment of Claims 1-4, 6, 7, 10, and 11; cancellation of Claims 8 and 9; and entry of new Claims 12-15. The Claim Listing below will replace all prior versions of the claims in the application:

Claim Listing

(Currently Amended) A method for the removal of airborne molecular contaminants
 (AMC) from a <u>surface substrate</u> comprising the steps of:

providing purifying a purge gas to produce a purified purge gas, wherein the purified purge gas comprises water at a concentration of at least about 100 parts per million (ppm) on a volume basis, and the purified purge gas has having an AMC concentration less than about 1 part per billion (ppb) on a volume basis;

contacting at least a portion of the surface substrate with the purified purge gas; producing a contaminated purge gas by transferring a portion of the contamination AMC from the surface substrate into the purified purge gas; and removing the contaminated purge gas from the surface substrate; thereby removing AMC from the substrate.

- 2. (Currently Amended) The method as in claim 1, wherein the steps are repeated until said contaminant concentration in the contaminated purge gas is has an AMC concentration below about 100 parts per trillion (ppt) on a volume basis.
- (Currently Amended) The method as in claim 1, wherein the <u>AMC concentration of</u>
 <u>the</u> purified purge gas has a contaminant concentration of <u>is</u> less than about 10 ppt
 AMC on a volume basis.
- 4. (Currently Amended) The method as in claim 1, wherein the <u>AMC concentration of the</u> purified purge gas has a contaminant concentration of <u>is</u> less than about 1 ppt AMC on a volume basis.

- 5. (Original) The method as in claim 1, wherein the water comprises 100 ppm to 2% by volume.
- 6. (Currently Amended) The method as in claim 1 further comprising purging of the device substrate with an inert gas after removing said contaminated <u>purge</u> gas from said substrate device.
- 7. (Currently Amended) The method as in claim 6, wherein said inert gas is selected from the group consisting of nitrogen, argon, nobel noble gases and methane.
- 8. (Cancelled)
- 9. (Cancelled)
- 10. (Currently Amended) The method as in claim 1, wherein the surface substrate is enclosed within a chamber comprises an interior surface of a device wherein the device encloses a space.
- 11. (Currently Amended) A The method as described in claim 10, wherein the substrate includes device encloses at least one silicon substrate.
- 12. (New) The method as in claim 1, whereby the steps of contacting at least a portion of the substrate with the purified purge gas, producing a contaminated purge gas, and removing the contaminated purge gas, thereby removes AMC from the substrate at a faster rate than the method using a purge gas consisting essentially of nitrogen gas.
- 13. (New) The method as in claim 12, wherein the substrate is contaminated with AMC before the substrate is contacted with purified purge gas.
- 14. (New) The method as in claim 10, wherein the substrate includes a wafer.

15. (New) A method for the removal of airborne molecular contaminants (AMC) from a substrate comprising the steps of:

providing a purified purge gas, wherein the purified purge gas comprises water, the purified purge gas having an AMC concentration less than about 1 part per billion (ppb) on a volume basis;

contacting at least a portion of the substrate with the purified purge gas;
producing a contaminated purge gas by transferring AMC from the substrate into
the purified purge gas; and

removing the contaminated purge gas from the substrate, wherein the water in the purified purge gas is in an amount sufficient to remove AMC from the substrate at a faster rate than the method using a purge gas consisting essentially of nitrogen gas.